TOSHIBA TA4016AFE

TOSHIBA BIPOLAR LINEAR INTEGRATED CIRCUIT SILICON MONOLITHIC

TA4016AFE

UHF WIDE BAND AMPLIFIER APPLICATIONS

FEATURES

Low Current $: I_{CC} = 6 \text{ mA}$

• Wide Band : f = 3.2 GHz (3 dB down)

Operating Supply Voltage : V_{CC} = 1.5~3 V

MAXIMUM RATINGS (Ta = 25°C)

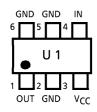
CHARACTERISTIC	SYMBOL	RATING	UNIT
Supply Voltage	Vcc	3.6	V
Total Power Dissipation	P _D (*)	100	mW
Operating Temperature	T _{opr}	- 40∼85	°C
Storage Temperature	T _{stg}	- 55~150	°C

SSOP6-P-0.5

Weight: 0.003 g (Typ.)

(*): When mounted on the glass epoxy of $2.5 \text{ cm}^2 \times 1.6 \text{ t}$

PIN ASSIGNMENT



CAUTION

This device electrostatic sensitivity. Please handle with caution.

- TOSHIBA is continually working to improve the quality and the reliability of its products. Nevertheless, semiconductor devices in general can malfunction or fail due to their inherent electrical sensitivity and vulnerability to physical stress. It is the responsibility of the buyer, when utilizing TOSHIBA products, to observe standards of safety, and to avoid situations in which a malfunction or failure of a TOSHIBA product could cause loss of human life, bodily injury or damage to property. In developing your designs, please ensure that TOSHIBA products are used within specified operating ranges as set forth in the most recent products specifications. Also, please keep in mind the precautions and conditions set forth in the TOSHIBA Semiconductor Reliability Handbook.

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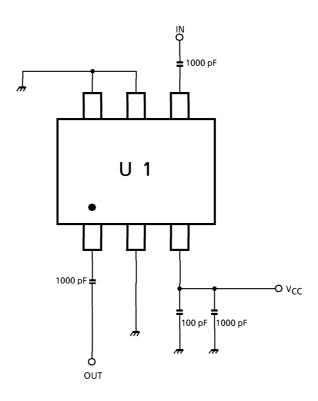
 The information contained herein is subject to change without notice.
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ELECTRICAL CHARACTERISTICS (Ta = 25°C, Zg = ZI = 50 Ω)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Circuit Current	lcc	V _{CC} = 2 V, Non carrier	4	6	8	mA
Band Width	BW	V _{CC} = 2 V (Note)	2.8	3.2	_	GHz
Insertion Gain	S21 ²	V _{CC} = 2 V, f = 1.5 GHz	17	19	22	dB
Noise Figure	NF	V _{CC} = 2 V, f = 1.5 GHz	_	4.5	6	dB
Isolation	S12 ²	V _{CC} = 2 V, f = 1.5 GHz	_	- 32	_	dB
Input Return Loss	S11 ²	V _{CC} = 2 V, f = 1.5 GHz	_	- 16	_	dB
Output Return Loss	S22 ²	V _{CC} = 2 V, f = 1.5 GHz	_	-7	_	dB
Output Power at 1dB Gain Compression	Po1dB	V _{CC} = 2 V, f = 1.5 GHz		-7	_	dBmW

(Note) : BW is the frequency of 3 dB down from $|S21|^2$ at 1.5 GHz.

TEST CIRCUIT



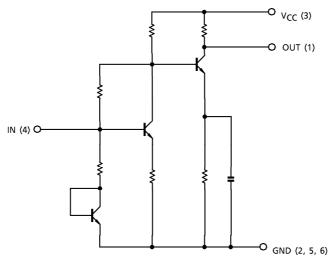
NOTICE

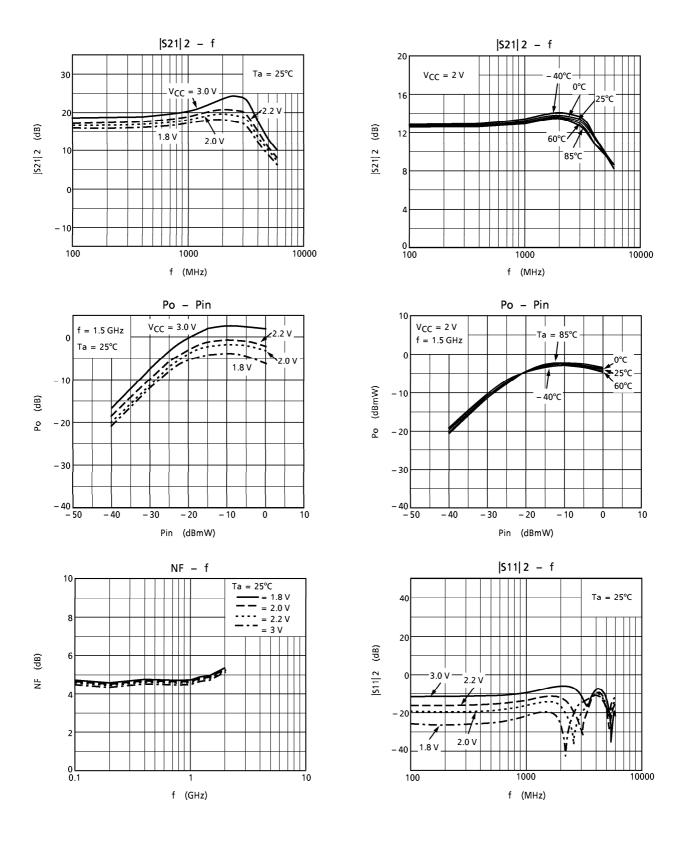
The circuits and measurements contained in this document are given only in the context of as examples of applications for these products.

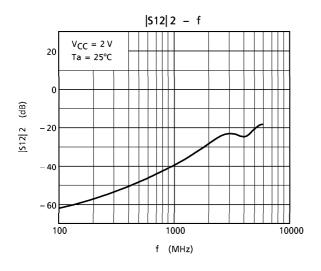
Moreover, these example application circuits are not intended for mass production, since the high-frequency characteristics (the AC characteristics) of these devices will be affected by the external components which the customer uses, by the design of the circuit and by various other conditions. It is the responsibility of the customer to design external circuits which correctly implement the intended application, and to check the characteristics of the design.

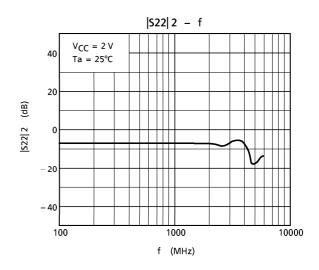
TOSHIBA assume no responsibility for the integrity of customer circuit designs or applications.

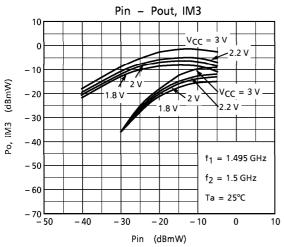
EQUIVALENT CIRCUIT

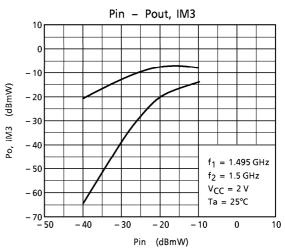


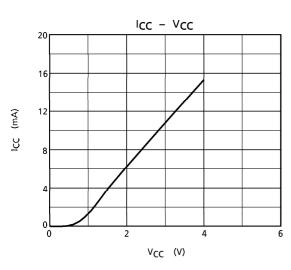






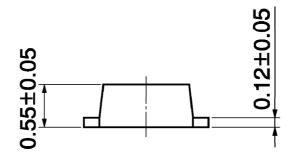






PACKAGE DIMENSIONS SSOP6-P-0.5

1.6±0.05 1.2±0.05 1.2±0.05 4 Unit: mm



Weight: 0.003 g (Typ.)